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Data Sheet Issue:- 1

Provisional Data

Wespack Rectifier Diode Types W4693QK050 to W4693QK080

Absolute Maximum Ratings

	VOLTAGE RATINGS)	MAXIMUM LIMITS	UNITS
V _{RRM}	Repetitive peak reverse voltage, (note 1)	\sim		500 - 800	V
V _{RSM}	Non-repetitive peak reverse voltage, (note 1)			600 – 900	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I _{F(AV)M}	Maximum average forward current, T _{sink} =55°C, (note 2)	4693	А
I _{F(AV)M}	Maximum average forward current. T _{sink} =100°C,/(note 2)	3399	А
I _{F(AV)M}	Maximum average forward current. T _{sink} =100°C, (note 3)	1786	А
I _{F(RMS)}	Nominal RMS forward current, T _{sink} =25°C, (note 2)	8561	А
I _{F(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 4)	6998	А
I _{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{m}=60\%V_{RRM}$, (note 5)	31.5	kA
I _{FSM2}	Peak non-repetitive surge t _p ≠10ms, V _m ≤10V, (note 5)	34.7	kA
l ² t	$I^{2}t$ capacity for fusing t _p =10ms, V _m =60%V _{RRM} , (note 5)	4.98×10 ⁶	A ² s
l ² t	I ² t capacity for fusing t₀=10ms, Vm≤10V, (note 5)	6.02×10 ⁶	A ² s
T _{j op}	Operating temperature range	-40 to +180	°C
T _{stg}	Storage temperature range	-55 to +180	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.

2) Double side cooled, single phase, 50Hz, 180° half-sinewave.

3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.

4) Double side cooled

5) Half-sinewave, 180°C T_i initial.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V _{FM}	Maximum peak forward voltage	-	-	1.05	IFM=3000A	V
V _{FM}	Maximum peak forward voltage	-	-	1.71	I _{FM} =14070A	V
V _{T0}	Threshold voltage	-	-	0.904		V
r _T	Slope resistance	-	-	0.057		mΩ
I _{RRM}	Peak reverse current	-	-	50	Rated V _{RRM}	mA
Q _{rr}	Recovered charge	-	1100	-		μC
Q _{ra}	Recovered charge, 50% Chord	-	940	1200	I _{TM} =1000A, t _p =1000μs, di/dt=10A/μs,	μC
l _{rm}	Reverse recovery current	-	120		Vr=50∀	А
t _{rr}	Reverse recovery time, 50% chord	-	15.5	ζ- <		μs
		-	-	0.0170	Double side cooled	K/W
R _{thJK}	Thermal resistance, junction to heatsink	-	-	0.0303	Anode side cooled	K/W
		-	-	0.0387	Cathode side cooled	K/W
F	Mounting force	16	- /	_20	Note 2	kN
Wt	Weight	-	200			g

Notes:-

1) Unless otherwise indicated $T_i=180^{\circ}C$.

2) For other clamp forces, please consult factory.

Notes on Ratings and Characteristics

1.0 Voltage Grade Table

				$\langle \cap \rangle$
Voltage Grade	V _{RRM} V	V _{RSM} V	\sim	
05	500	600		340
08	800	900	2	560

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by/Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable/to this device for Tibelow 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

Where V_{T0} =0.904V, r_T=0.057m Ω ,

 R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

	Supplementary The	ermal Impedance		
Conduction Angle	(6 phase (60°)	3 phase (120°)	¹ ⁄ ₂ wave (180°)	d.c.
Square wave Double Side Cooled	0.0231	0.0207	0.0192	0.0170
Square wave Cathode Side Cooled	0.0417	0.0408	0.0398	0.0387
Sine wave Double Side Cooled	0.0208	0.0181	0.0170	
Sine wave Cathode Side Cooled	0.0404	0.0396	0.0387	

Form Factors					
Conduction Angle	6 phase (60°)	3 phase (120°)	¹ ⁄ ₂ wave (180°)	d.c.	
Square wave	2.449	1.732	1.414	1	
Sine-wave	2.778	1.879	1.57		

5.2 Calculating V_F using ABCD Coefficients

The on-state characteristic I_F vs. V_F, on page 6 is represented in two ways;

- (i) the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_F in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

	25°C Coefficients		180°C Coefficients
А	0.8298867	Α	0.5863875
В	9.155618×10 ⁻³	В	0.01531595
С	2.050282×10 ⁻⁵	(C	3.126409×10⁻⁵
D	3.903746×10 ⁻³	Q	4.513144×10 ⁻³

5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}} \right)$$

Where p = 1 to *n*, *n* is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- r_{t} = Thermal resistance at time t.
- r_p = Amplitude of p_{th} term.
- τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below.

Term 1 2 3 4 r_p 0.01054152 4.166135×10 ⁻³ 9.048202×10 ⁻⁴ 1.404721×1	
$r_{\rm c}$ 0.01054152 4.166135×10 ⁻³ 9.048202×10 ⁴ 1.404721×1	
<i>T_p</i> 0.01034132 4.100133×10 9.040202×10 × 1.404721×1) ⁻³
τ _p 0.2322298 0.05315938 0.0151575 2.630485×1) ⁻³

D.C. Cathode Side Cooled					
Term	1	2	3		
r _p	0.02947555	7:046786×10 ⁻³	2.102936×10 ⁻³		
τρ	1.276137	0.0795146	3.881676×10 ⁻³		

6.0 Reverse recovery ratings





di_R/dt

50 % I_{RM}

(ii) Q_{rr} is based on a 150µs integration time i.e.



Curves



Figure 2 - Transient thermal impedance





Figure 8 – Forward current vs. Power dissipation – Double Side Cooled

Figure 9 – Forward current vs. Heatsink temperature – Double Side Cooled



Eigure 11 – Forward current vs. Heatsink temperature – Cathode Side Cooled



5000

Outline Drawing & Ordering Information

